



30V Complementary Enhancement Mode MOSFET - ESD Protected

Voltage

30 / -30V

Current

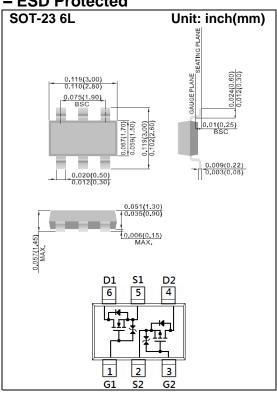
1.6 /-1.1A

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: SC0



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMET	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	-30	V
Gate-Source Voltage		V_{GS}	<u>+</u> 8	<u>+</u> 8	V
Continuous Drain Current		I _D	1.6	-1.1	А
Pulsed Drain Current (Note 4)		I _{DM}	6.4	-4.4	А
	T _a =25°C	1	1.25		W
Power Dissipation	Derate above 25°C	P_{D}	1	mW/°C	
Operating Junction and Storage	T_{J}, T_{STG}	-55~150		°C	
Typical Thermal resistance					
- Junction to Ambient (Note 3)		$R_{\theta JA}$	100		°C/W
			1		





N-Channel Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.5	0.78	1.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =1.6A	-	145	200	
		V _{GS} =2.5V, I _D =1.1A	-	185	270	mΩ
		V _{GS} =1.8V, I _D =0.2A	-	330	570	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	0.01	1	uA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$	-	1.4	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	Q_g	\/ 45\/ 4.6A	-	1.5	-	nC
Gate-Source Charge	Q_gs	V_{DS} =15V, I_{D} =1.6A, V_{GS} =4.5V (Note 1,2)	-	0.3	-	
Gate-Drain Charge	Q_gd	V _{GS} =4.5 V	-	0.3	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	93	-	pF
Output Capacitance	Coss		-	19	-	
Reverse Transfer Capacitance	Crss		-	6	-	
Turn-On Delay Time	td _(on)	\/ 45\/ 4.64	-	6.4	-	
Turn-On Rise Time	tr	V_{DD} =15V, I_{D} =1.6A, V_{GS} =4.5V, R_{G} =6 Ω (Note 1,2)	-	33	-	ns
Turn-Off Delay Time	td _(off)		-	37	-	
Turn-Off Fall Time	tf		-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S		-	-	1.0	А
Diode Forward Voltage	V _{SD}	I _S = 1.0A, V _{GS} =0V	-	0.81	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing





P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-0.5	-0.98	-1.3	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-1.1A	-	293	370	mΩ
		V _{GS} =-2.5V, I _D =-0.5A	-	387	540	
		V _{GS} =-1.8V, I _D =-0.1A	-	750	970	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I _{GSS}	$V_{GS}=\underline{+}8V, V_{DS}=0V$	-	<u>+</u> 3.4	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	Q_g	V _{DS} =-15V, I _D =-1.1A, V _{GS} =-4.5V (Note 1,2)	-	1.6	-	nC
Gate-Source Charge	Q_gs		-	0.5	-	
Gate-Drain Charge	Q_gd		-	0.3	-	
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V, f=1.0MHZ	-	125	-	pF
Output Capacitance	Coss		-	22	-	
Reverse Transfer Capacitance	Crss		-	6	-	
Turn-On Delay Time	td _(on)	\/ 45\/ L 44A	-	11	-	
Turn-On Rise Time	tr	V_{DD} =-15V, I_{D} =-1.1A, V_{GS} =-4.5V, R_{G} =6 Ω (Note 1.2)	-	51	-	ns
Turn-Off Delay Time	td _(off)		-	65	-	
Turn-Off Fall Time	tf	K _G =012	-	46	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					-1.0	Α
Diode Forward Current	I _S		-	-	-1.0	А
Diode Forward Voltage	V_{SD}	I _S =-1.0A, V _{GS} =0V	-	-0.9	-1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
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N-Channel TYPICAL CHARACTERISTIC CURVES

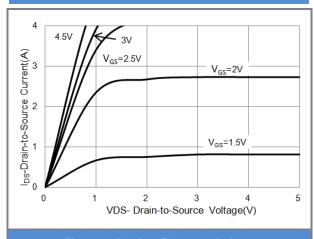


Fig.1 On-Region Characteristics

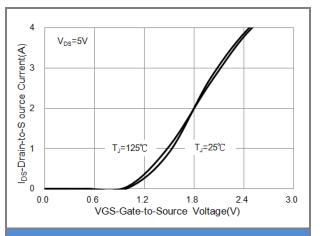


Fig.2 Transfer Characteristics

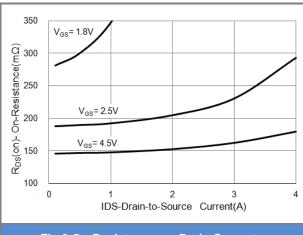


Fig.3 On-Resistance vs. Drain Current

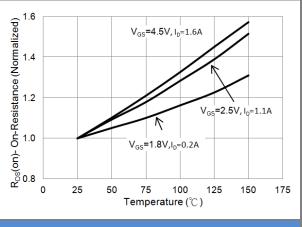
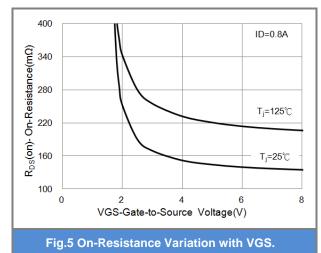
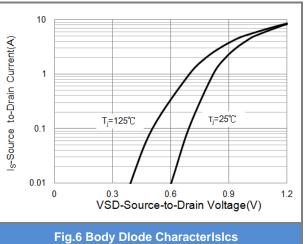


Fig.4 On-Resistance vs. Junction temperature











N-Channel TYPICAL CHARACTERISTIC CURVES

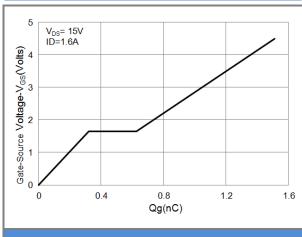


Fig.7 Gate-Charge Characteristics

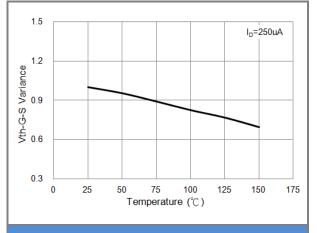


Fig.8 Threshold Voltage Variation with Temperature.

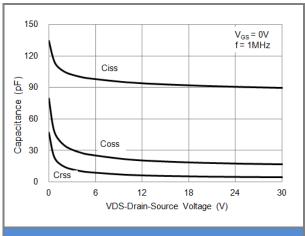


Fig.9 Capacitance vs. Drain-Source Voltage.





P-Channel TYPICAL CHARACTERISTIC CURVES

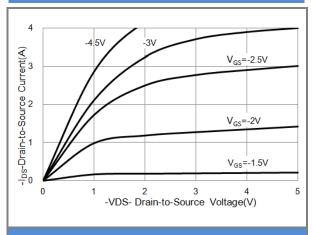


Fig.1 On-Region Characteristics

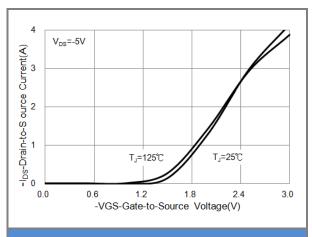


Fig.2 Transfer Characteristics

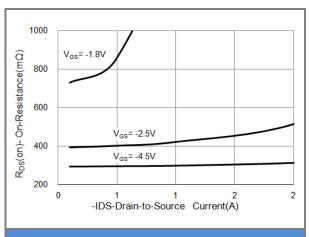


Fig.3 On-Resistance vs. Drain Current

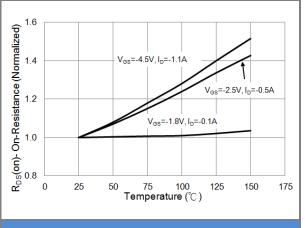


Fig.4 On-Resistance vs. Junction temperature

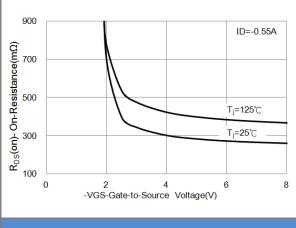
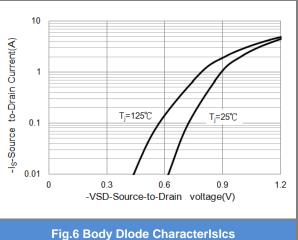


Fig.5 On-Resistance Variation with VGS.







P-Channel TYPICAL CHARACTERISTIC CURVES

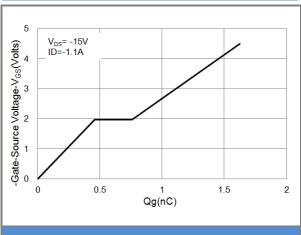


Fig.7 Gate-Charge Characteristics

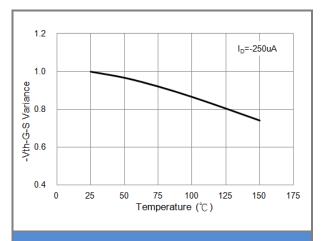


Fig.8 Threshold Voltage Variation with Temperature.

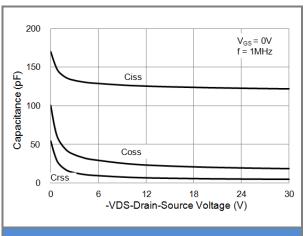


Fig.9 Threshold Voltage Variation with Temperature.

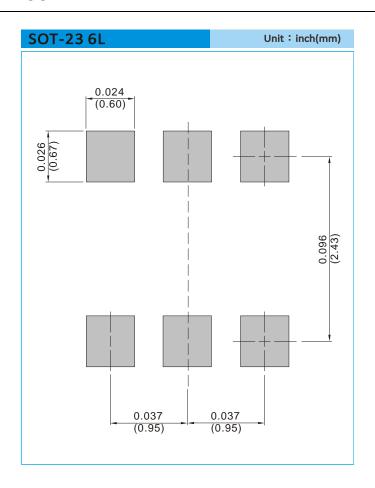




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6600_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC0	Halogen free
PJS6600_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC0	Halogen free

MOUNTING PAD LAYOUT







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